

Bhavtosh Bansal

List of Publications by Year in descending order

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docs citations

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times ranked

845
citing authors

#	ARTICLE	IF	CITATIONS
1	Dissipation-induced symmetry breaking: Emphanitic transitions in lead- and tin-containing chalcogenides and halide perovskites. Applied Physics Letters, 2021, 118, .	1.5	5
2	Absolute calibration of the latent heat of transition using differential thermal analysis. Review of Scientific Instruments, 2021, 92, 075106.	0.6	1
3	Experimental determination of the bare energy gap of GaAs without the zero-point renormalization. Journal of Physics Condensed Matter, 2020, 32, 10LT01.	0.7	2
4	Competition between two- and three-photon upconversion in Er ³⁺ -doped microcrystals. Journal of Luminescence, 2020, 227, 117542.	1.5	8
5	Highly Sensitive Upconverting Nanoplatfrom for Luminescent Thermometry from Ambient to Cryogenic Temperature. ChemPhysChem, 2020, 21, 1731-1736.	1.0	12
6	Critical Slowing Down at the Abrupt Mott Transition: When the First-Order Phase Transition Becomes Zeroth Order and Looks Like Second Order. Physical Review Letters, 2020, 124, 095703.	2.9	18
7	Classification of Transitions in Upconversion Luminescence of Lanthanides by Two-Dimensional Correlation Analysis. Journal of Physical Chemistry A, 2019, 123, 2457-2461.	1.1	6
8	Distinguishing quantum dot-like localized states from quantum well-like extended states across the exciton emission line in a quantum well. Journal of Physics Condensed Matter, 2018, 30, 105402.	0.7	2
9	How pump-probe differential reflectivity at negative delay yields the perturbed-free-induction-decay: theory of the experiment and its verification. Journal of Physics Condensed Matter, 2018, 30, 505902.	0.7	4
10	Kinetic Spinodal Instabilities in the Mott Transition in V_2O_3 . Physical Review Letters, 2018, 121, 045701.	2.9	16
11	Evidence from Hysteresis Scaling and Dissipative Phase Ordering. Physical Review Letters, 2018, 121, 045701.	2.9	16
12	Measurements of the Electric Field of Zero-Point Optical Phonons in GaAs Quantum Wells Support the Urbach Rule for Zero-Temperature Lifetime Broadening. Physical Review Letters, 2015, 114, 047402.	2.9	16
13	Anomalous effects of ultradilute impurities on heat diffusion in liquids. Optics Communications, 2015, 334, 184-189.	1.0	4
14	Self-Assembly in Semiconductor Epitaxy. , 2015, , 1057-1099.		7
15	Khatua, Bansal, and Shahar Reply:. Physical Review Letters, 2014, 113, 158902.	2.9	1
16	Optical density of states in ultradilute GaAsN alloy: Coexistence of free excitons and impurity band of localized and delocalized states. Journal of Applied Physics, 2014, 116, 023103.	1.1	16
17	Anti-Stokes luminescence in the light of second order perturbation theory. Applied Physics Letters, 2014, 105, 191102.	1.5	1
18	Single-Slit Electron Diffraction with Aharonov-Bohm Phase: Feynman's Thought Experiment with Quantum Point Contacts. Physical Review Letters, 2014, 112, 010403.	2.9	14
19	Pauli blocking dynamics in optically excited quantum dots: A picosecond excitation-correlation spectroscopic study. Physical Review B, 2013, 87, .	1.1	7

#	ARTICLE	IF	CITATIONS
19	Scattering of carriers by charged dislocations in semiconductors. Journal of Applied Physics, 2013, 113, 163705.	1.1	1
20	Light emission despite doubly-forbidden radiative transitions in AlP/GaP quantum wells: Role of localized states. Journal of Applied Physics, 2013, 114, 163101.	1.1	2
21	On conversion of luminescence into absorption and the van Roosbroeck-Shockley relation. Applied Physics Letters, 2012, 100, 222103.	1.5	62
22	High-field magneto-photoluminescence of semiconductor nanostructures. Luminescence, 2012, 27, 179-196.	1.5	22
23	Charge separation and temperature-induced carrier migration in Ga _{1-x} In _x NyAs _{1-y} quantum wells. Applied Physics Letters, 2006, 89, 032110.	1.5	17
24	Fiber optic based system for polarization sensitive spectroscopy of semiconductor quantum structures. Review of Scientific Instruments, 2010, 81, 083901.	0.6	5
25	Extended excitons and compact heliumlike biexcitons in type-II quantum dots. Physical Review B, 2009, 80, .	1.1	30
26	Excitonic Mott transition in type-II quantum dots. Physical Review B, 2008, 77, .	1.1	20
27	Photoluminescence from localized states in disordered indium nitride. Applied Physics Letters, 2008, 93, 021113.	1.5	13
28	Alloying induced degradation of the absorption edge of InAs _{1-x} Sb _x . Applied Physics Letters, 2007, 90, 101905.	1.5	20
29	InAs/InP quantum dots with bimodal size distribution: Two evolution pathways. Journal of Applied Physics, 2007, 101, 094303.	1.1	17
30	Magnetic field-dependent photoluminescence linewidths as a probe of disorder length scales in quantum wells. Applied Physics Letters, 2007, 91, 251108.	1.5	13
31	Tuning and understanding the emission characteristics of MOVPE-grown self-assembled InAs/InP quantum dots. Journal of Crystal Growth, 2007, 298, 586-590.	0.7	5
32	A model for the temperature dependence of photoluminescence from self-assembled quantum dots. Journal of Applied Physics, 2006, 100, 093107.	1.1	21
33	Alloy disorder effects on the room temperature optical properties of Ga _{1-x} In _x NyAs _{1-y} quantum wells. Applied Physics Letters, 2006, 89, 032110.	1.5	17
34	Detailed studies on the origin of nitrogen-related electron traps in dilute GaAsN layers grown by liquid phase epitaxy. Semiconductor Science and Technology, 2005, 20, 1168-1172.	1.0	16
35	Magnetic field induced band depopulation in intrinsic InSb: a revisit. Journal of Physics Condensed Matter, 2005, 17, 7053-7060.	0.7	2
36	Growth kinetics effects on self-assembled InAs _{1-x} InP quantum dots. Applied Physics Letters, 2005, 87, 203104.	1.5	12

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37	Collapse of the charge-ordering state at high magnetic fields in the rare-earth manganite $\text{Pr}_{0.63}\text{Ca}_{0.37}\text{MnO}_3$. <i>Physical Review B</i> , 2005, 71, .	1.1	15
38	Studies on high resolution x-ray diffraction, optical and transport properties of $\text{InAs}_x\text{Sb}_{1-x}\text{GaAs}$ ($x \approx 0.06$) heterostructure grown using liquid phase epitaxy. <i>Journal of Applied Physics</i> , 2004, 96, 4989-4997.	1.1	23
39	Transport, optical and magnetotransport properties of hetero-epitaxial $\text{InAs}_x\text{Sb}_{1-x}/\text{GaAs}$ ($x \approx 0.06$) and bulk crystals: experiment and theoretical analysis. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 20, 272-277.	1.3	4
40	Magnetic, optical and transport properties of GaMnN films. <i>Solid State Communications</i> , 2003, 125, 55-57.	0.9	35
41	Temperature dependence of the energy gap and free carrier absorption in bulk $\text{InAs}_{0.05}\text{Sb}_{0.95}$ single crystals. <i>Applied Physics Letters</i> , 2003, 82, 4720-4722.	1.5	16
42	Structural, optical, and electrical properties of bulk single crystals of $\text{InAs}_x\text{Sb}_{1-x}$ grown by rotatory Bridgman method. <i>Applied Physics Letters</i> , 2002, 81, 1630-1632.	1.5	15
43	High-mobility InSb epitaxial films grown on a GaAs (001) substrate using liquid-phase epitaxy. <i>Applied Physics Letters</i> , 2002, 80, 2102-2104.	1.5	18